

SCHOTTKY DIE SPECIFICATION

TYPE: SB16100

General Description: 100V 15 A Standard VF

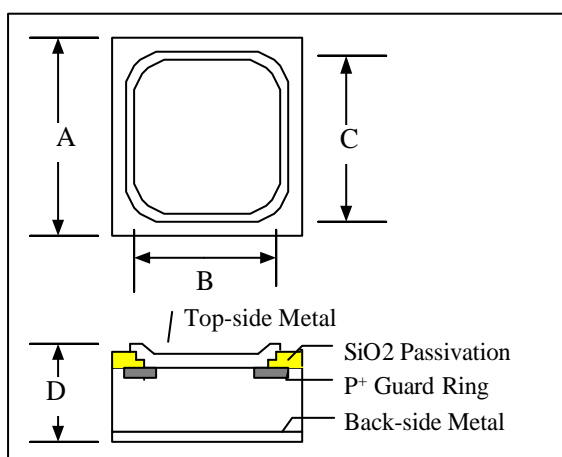
Single Anode

ELECTRICAL CHARACTERISTICS	SYM	Spec. Limit	Die Sort	UNIT
DC Blocking Voltage: Ir=1mA(for wafer form)	VRRM	100	105	Volt
Ir=0.5mA (for dice form)				
Average Rectified Forward Current	IFAV	15		Amp
Maximum Instantaneous Forward Voltage				
@ 15 Ampere, Ta=25°C	VF MAX	0.82	0.81	Volt
Maximum Instantaneous Reverse Voltage				
@ VR= 100 Volt, Ta=25°C	IR MAX	0.2	0.18	mA
Maximum Junction Capacitance @ 0V, 1MHZ	Cj MAX			pF
MAXIMUM RATINGS				
Nonrepetitive Peak Surge Current	IFSM	250		Amp
Operating Junction Temperature	TJ	-65 to +125		°C
Storage Temperature	TSTG	-65 to +125		°C

Specifications apply to die only. Actual performance may degrade when assembled.

MEMT does not guarantee device performance after assembly.

Data sheet information is subjected to change without notice.

DICE OUTLINE DRAWING


DIM	ITEM	um ²	Mil ²
A	Die Size	3116	122.67
B	Top Metal Pad Size	3016	118.70
C	Passivation Seal	3036	119.50
D	Thickness (Min)	254	10.00
	Thickness (Max)	305	12.00

PS:

(1)Cutting street width is around 80um(3.14mil).

(2)Both of top-side and back-side metals are Ti/Ni/Ag.